

DATA SHEET

74ABT125 Quad buffer (3-State)

Product specification
Supersedes data of 1996 Mar 05
IC23 Data Handbook

1998 Jan 16

Quad buffer (3-State)

74ABT125

FEATURES

- Quad bus interface
- 3-State buffers
- Live insertion/extraction permitted
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- Power-up 3-State
- Inputs are disabled during 3-State mode

DESCRIPTION

The 74ABT125 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT125 device is a quad buffer that is ideal for driving bus lines. The device features four Output Enables ($\overline{OE}0$, $\overline{OE}1$, $\overline{OE}2$, $\overline{OE}3$), each controlling one of the 3-State outputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS $T_{amb} = 25^{\circ}\text{C}; \text{GND} = 0\text{V}$	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay An to Yn	$C_L = 50\text{pF}; V_{CC} = 5\text{V}$	2.9	ns
C_{IN}	Input capacitance	$V_I = 0\text{V or } V_{CC}$	4	pF
C_{OUT}	Output capacitance	Outputs disabled; $V_O = 0\text{V or } V_{CC}$	7	pF
I_{CCZ}	Total supply current	Outputs disabled; $V_{CC} = 5.5\text{V}$	65	μA

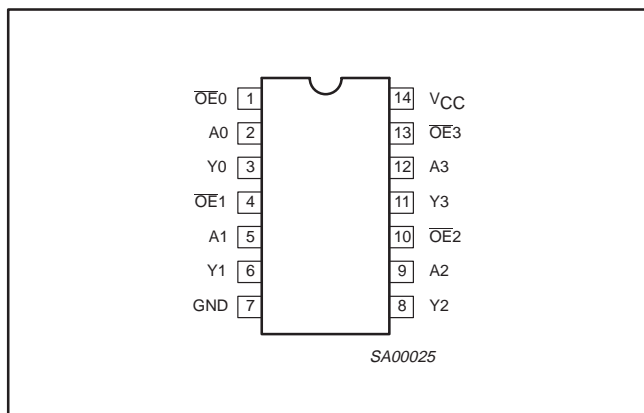
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic DIP	-40°C to +85°C	74ABT125 N	74ABT125 N	SOT27-1
14-Pin plastic SO	-40°C to +85°C	74ABT125 D	74ABT125 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT125 DB	74ABT125 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT125 PW	74ABT125PW DH	SOT402-1

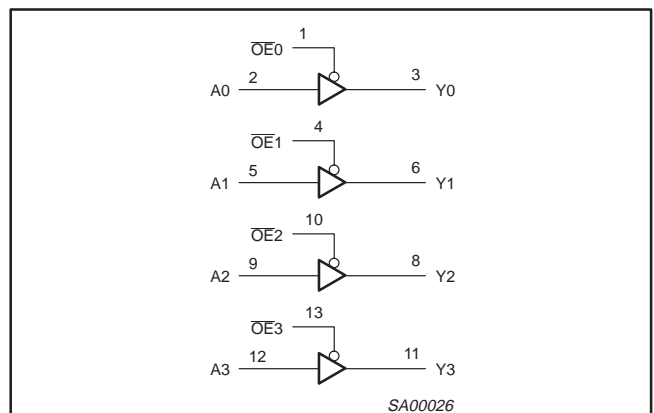
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
2, 5, 9, 12	A0 – A3	Data inputs
3, 6, 8, 11	Y0 – Y3	Data outputs
1, 4, 10, 13	$\overline{OE}0$ – $\overline{OE}3$	Output enable inputs (active-Low)
7	GND	Ground (0V)
14	V_{CC}	Positive supply voltage

PIN CONFIGURATION



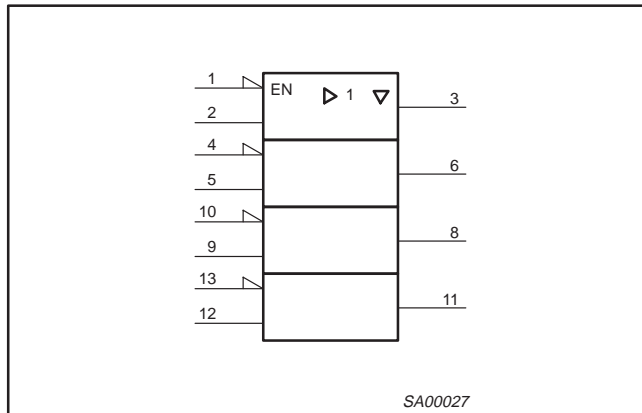
LOGIC SYMBOL



Quad buffer (3-State)

74ABT125

LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INPUTS		OUTPUTS
$\overline{O}E_n$	A_n	Y_n
L	L	L
L	H	H
H	X	Z

H = High voltage level
 L = Low voltage level
 X = Don't care
 Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		-0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	-18	mA
V_I	DC input voltage ³		-1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	-50	mA
V_{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	128	mA
T_{stg}	Storage temperature range		-65 to 150	°C

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		MIN	MAX	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Low-level input voltage		0.8	V
I_{OH}	High-level output current		-32	mA
I_{OL}	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_{amb}	Operating free-air temperature range	-40	+85	°C

Quad buffer (3-State)

74ABT125

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			T _{amb} = +25°C			T _{amb} = -40°C to +85°C		
			Min	Typ	Max	Min	Max	
V _{IK}	Input clamp voltage	V _{CC} = 4.5V; I _{IK} = -18mA		-0.9	-1.2		-1.2	V
V _{OH}	High-level output voltage	V _{CC} = 4.5V; I _{OH} = -3mA; V _I = V _{IL} or V _{IH}	2.5	2.9		2.5		V
		V _{CC} = 5.0V; I _{OH} = -3mA; V _I = V _{IL} or V _{IH}	3.0	3.4		3.0		V
		V _{CC} = 4.5V; I _{OH} = -32mA; V _I = V _{IL} or V _{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output voltage	V _{CC} = 4.5V; I _{OL} = 64mA; V _I = V _{IL} or V _{IH}		0.35	0.55		0.55	V
I _I	Input leakage current	V _{CC} = 5.5V; V _I = GND or 5.5V		±0.01	±1.0		±1.0	µA
I _{OFF}	Power-off leakage current	V _{CC} = 0.0V; V _O or V _I ≤ 4.5V		±5.0	±100		±100	µA
I _{PU} /I _{PD}	Power-up/down 3-State output current ³	V _{CC} = 2.1V; V _O = 0.5V; V _I = GND or V _{CC} ; V _{OE} = Don't care		±5.0	±50		±50	µA
I _{OZH}	3-State output High current	V _{CC} = 5.5V; V _O = 2.7V; V _I = V _{IL} or V _{IH}		1.0	50		50	µA
I _{OZL}	3-State output Low current	V _{CC} = 5.5V; V _O = 0.5V; V _I = V _{IL} or V _{IH}		-1.0	-50		-50	µA
I _{CEX}	Output High leakage current	V _{CC} = 5.5V; V _O = 5.5V; V _I = GND or V _{CC}		5.0	50		50	µA
I _O	Output current ¹	V _{CC} = 5.5V; V _O = 2.5V	-50	-100	-180	-50	-180	mA
I _{CCH}	Quiescent supply current	V _{CC} = 5.5V; Outputs High, V _I = GND or V _{CC}		65	250		250	µA
I _{CCL}		V _{CC} = 5.5V; Outputs Low, V _I = GND or V _{CC}		12	15		30	mA
I _{CCZ}		V _{CC} = 5.5V; Outputs 3-State; V _I = GND or V _{CC}		65	250		50	µA
ΔI _{CC}	Additional supply current per input pin ²	Outputs enabled, one data input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.5	1.5		1.5	mA
		Outputs 3-State, one data input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		50	250		250	µA
		Outputs 3-State, one enable input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.5	1.5		1.5	mA

NOTES:

- Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- This is the increase in supply current for each input at 3.4V.
- This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to 10msec. From V_{CC} = 2.1V to V_{CC} = 5V ± 10% a transition time of up to 100µsec is permitted.

AC CHARACTERISTICS

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF, R_L = 500Ω

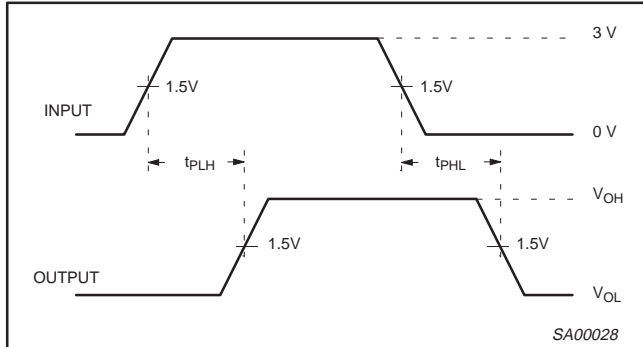
SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT
			T _{amb} = +25°C V _{CC} = +5.0V			T _{amb} = -40°C to +85°C V _{CC} = +5.0V ±0.5V		
			MIN	TYP	MAX	MIN	MAX	
t _{PLH} t _{PHL}	Propagation delay A _n to Y _n	1	1.0 1.0	2.8 3.1	4.1 4.6	1.0 1.0	4.6 4.9	ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	2	1.0 1.0	3.2 4.2	5.0 6.2	1.0 1.0	5.9 6.8	ns
t _{PHZ} t _{PLZ}	Output disable time from High and Low level	2	1.0 1.5	4.1 2.8	5.4 5.0	1.0 1.5	6.2 5.5	ns

Quad buffer (3-State)

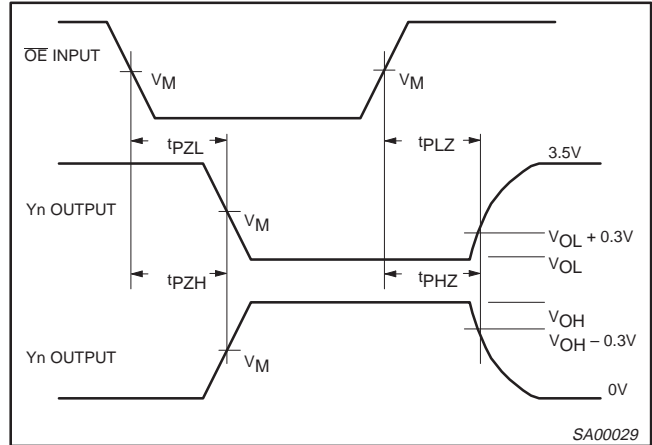
74ABT125

AC WAVEFORMS

$V_M = 1.5V, V_{IN} = GND \text{ to } 3.0V$



Waveform 1. Waveforms Showing the Input (An) to Output (Yn) Propagation Delays



Waveform 2. Waveforms Showing the 3-State Output Enable and Disable Times

TEST CIRCUIT AND WAVEFORMS

TEST	S1
t_{pd}	open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	open

DEFINITIONS
 $C_L =$ Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

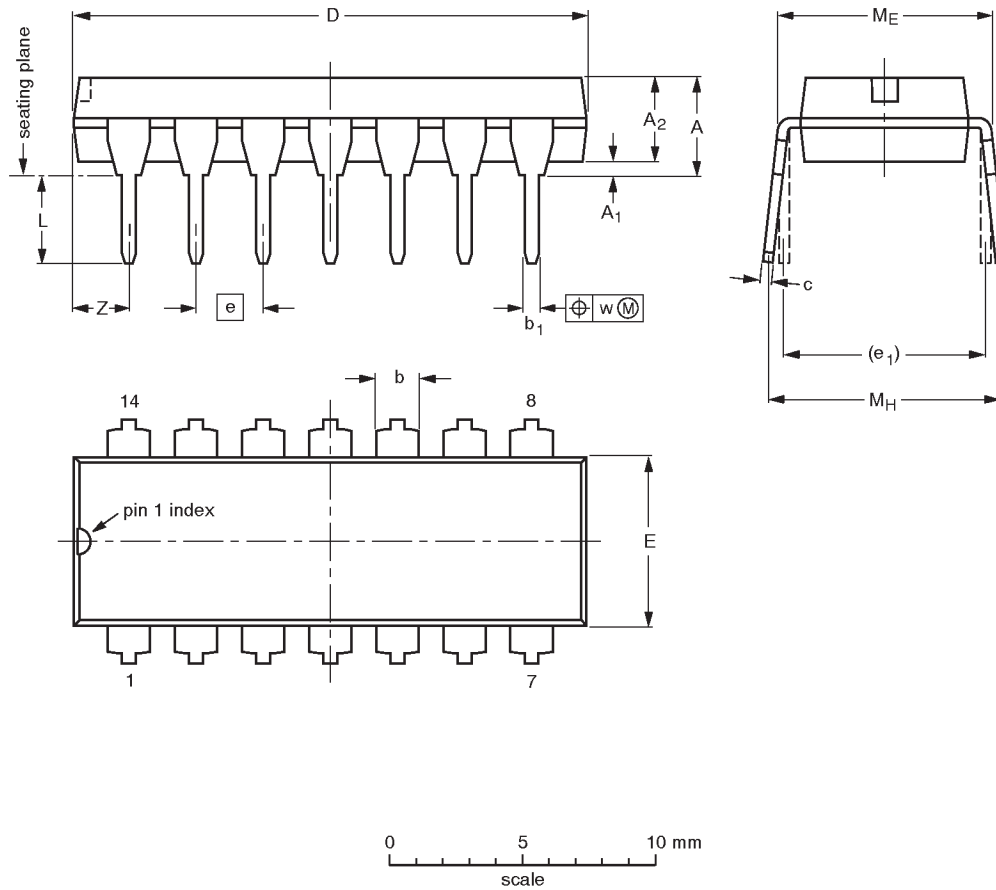
SA00012

Quad buffer (3-State)

74ABT125

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

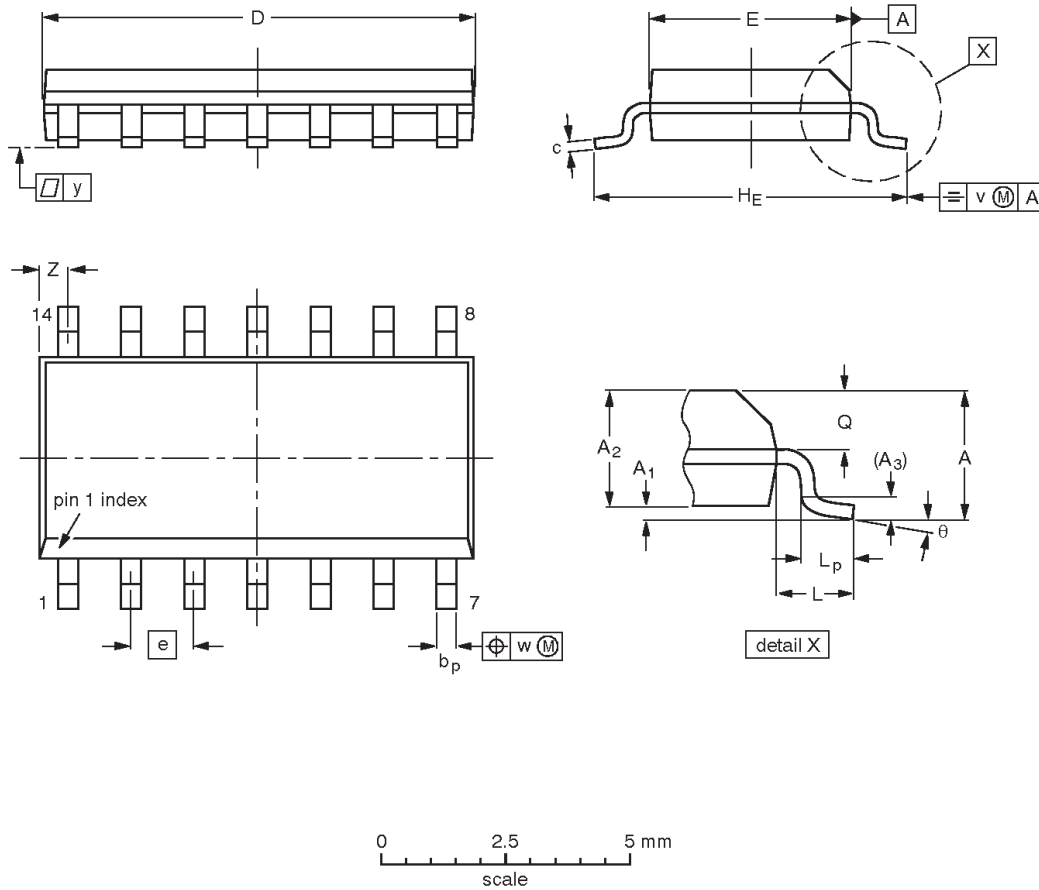
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT27-1	050G04	MO-001AA				92-11-17 95-03-11

Quad buffer (3-State)

74ABT125

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

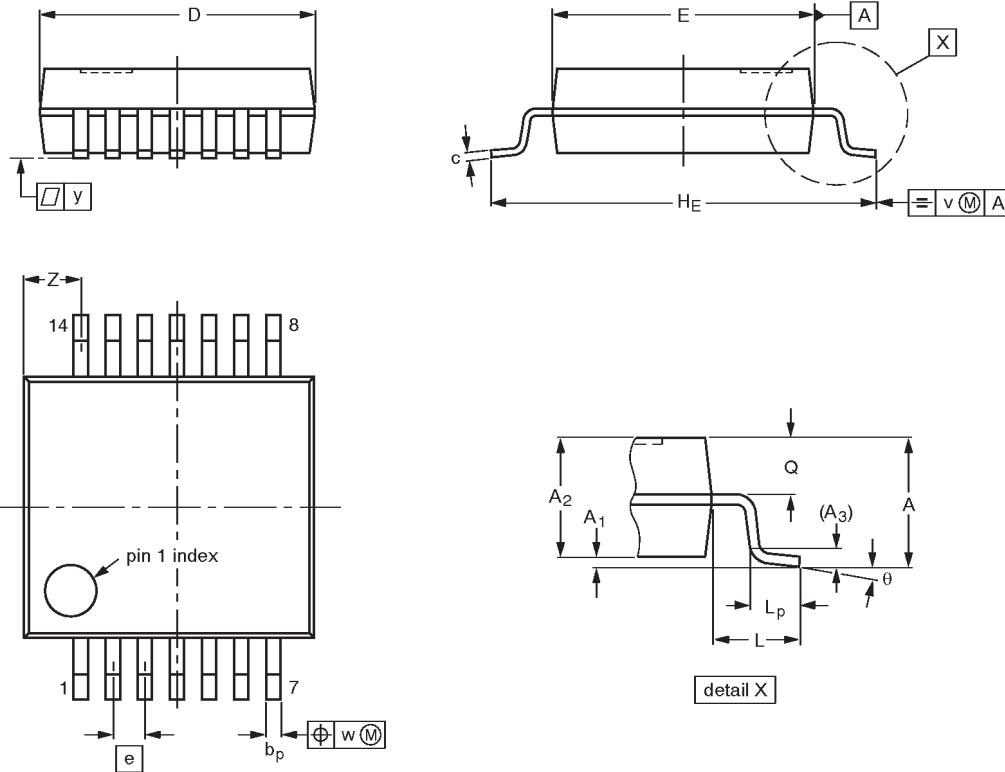
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT108-1	076E06S	MS-012AB				95-01-23 97-05-22

Quad buffer (3-State)

74ABT125

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

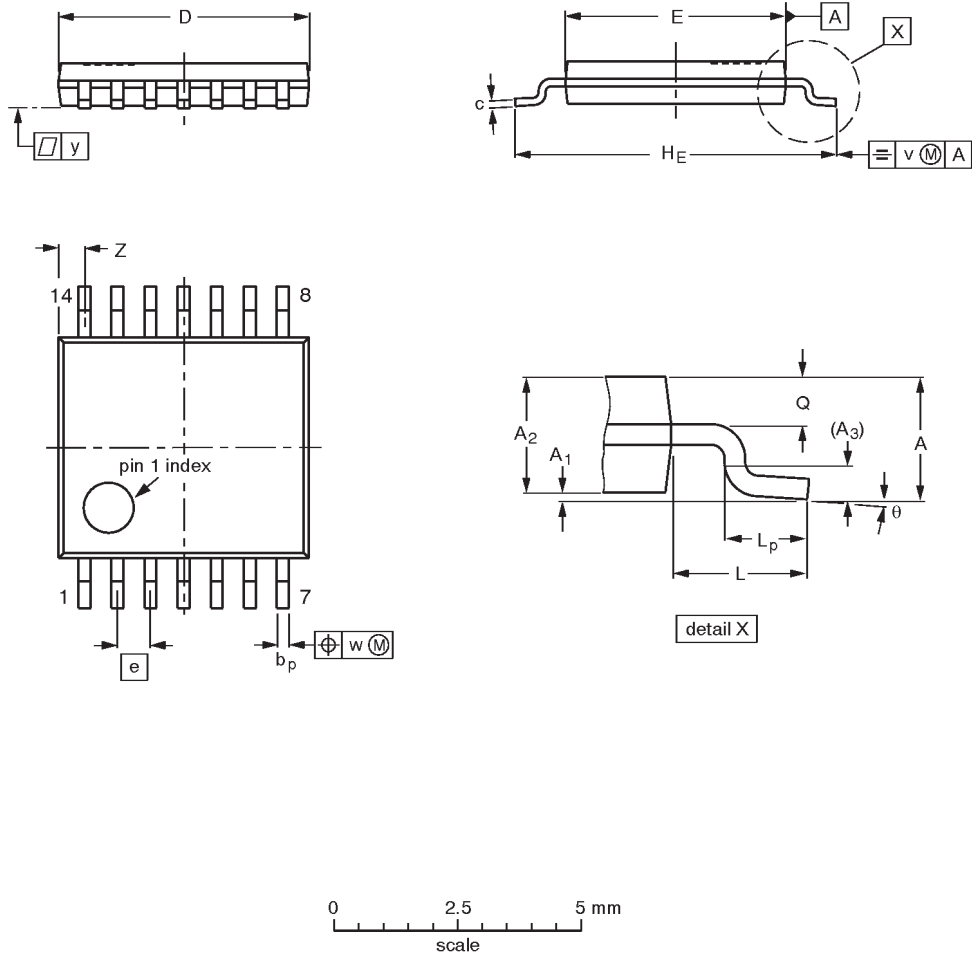
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT337-1		MO-150AB				95-02-04 96-01-18

Quad buffer (3-State)

74ABT125

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT402-1		MO-153				94-07-12 95-04-04

Quad buffer (3-State)

74ABT125

DEFINITIONS

Data Sheet Identification	Product Status	Definition
<i>Objective Specification</i>	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
<i>Preliminary Specification</i>	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
<i>Product Specification</i>	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.

Philips Semiconductors and Philips Electronics North America Corporation reserve the right to make changes, without notice, in the products, including circuits, standard cells, and/or software, described or contained herein in order to improve design and/or performance. Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified. Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

LIFE SUPPORT APPLICATIONS

Philips Semiconductors and Philips Electronics North America Corporation Products are not designed for use in life support appliances, devices, or systems where malfunction of a Philips Semiconductors and Philips Electronics North America Corporation Product can reasonably be expected to result in a personal injury. Philips Semiconductors and Philips Electronics North America Corporation customers using or selling Philips Semiconductors and Philips Electronics North America Corporation Products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors and Philips Electronics North America Corporation for any damages resulting from such improper use or sale.

Philips Semiconductors
811 East Arques Avenue
P.O. Box 3409
Sunnyvale, California 94088-3409
Telephone 800-234-7381

Philips Semiconductors and Philips Electronics North America Corporation register eligible circuits under the Semiconductor Chip Protection Act.
 © Copyright Philips Electronics North America Corporation 1998
 All rights reserved. Printed in U.S.A.

(print code)

Date of release: July 1994

Document order number:

9397-750-03613